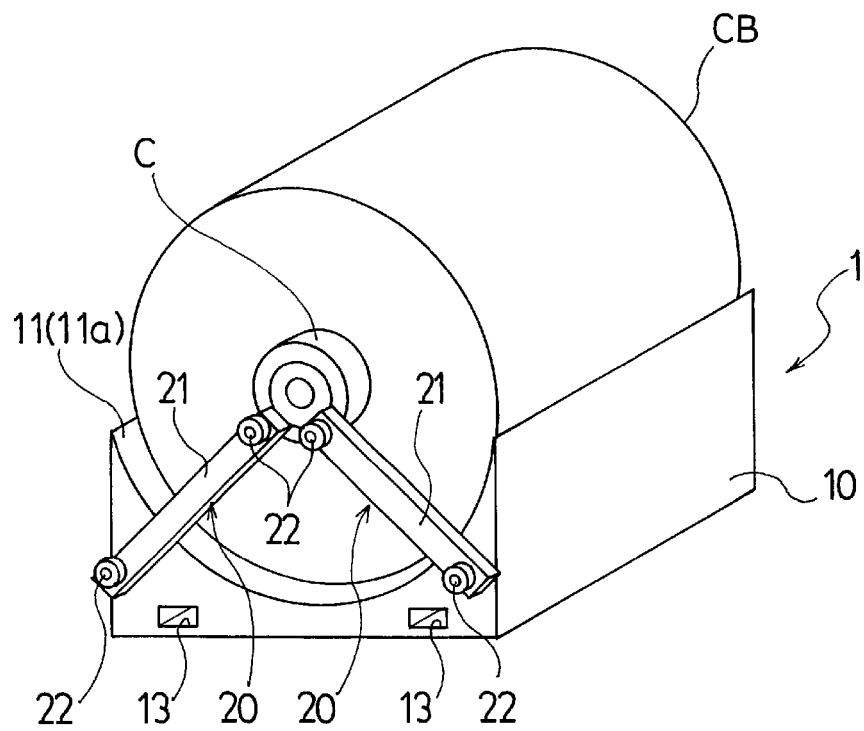


[図1]



[図2]

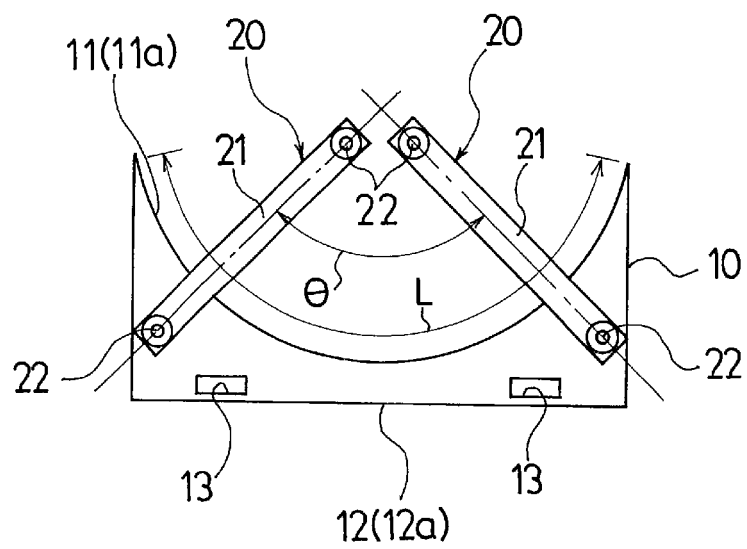
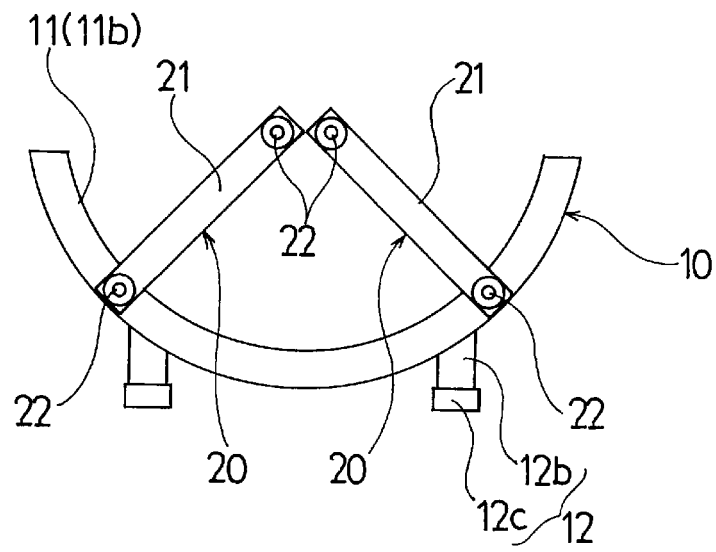
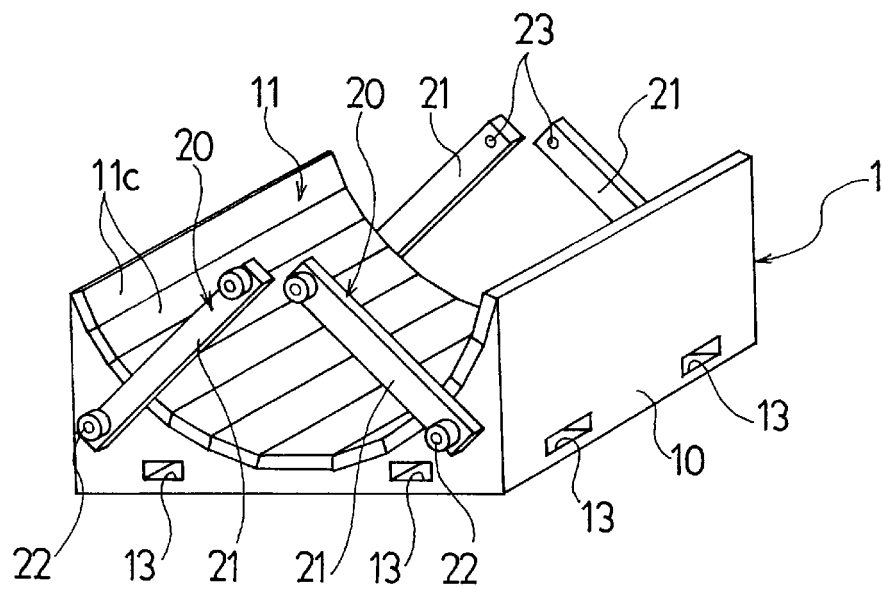


Diagram illustrating a cross-sectional view of a semiconductor device 100. The device includes a substrate 10, a central layer 11, and two regions 21 flanking the central layer 11. Regions 22 are located on the outer sides of regions 21. A layer 12(12a) is positioned above the substrate 10, and a layer CB is positioned above layer 12(12a). A layer C is positioned on the right side of the device.

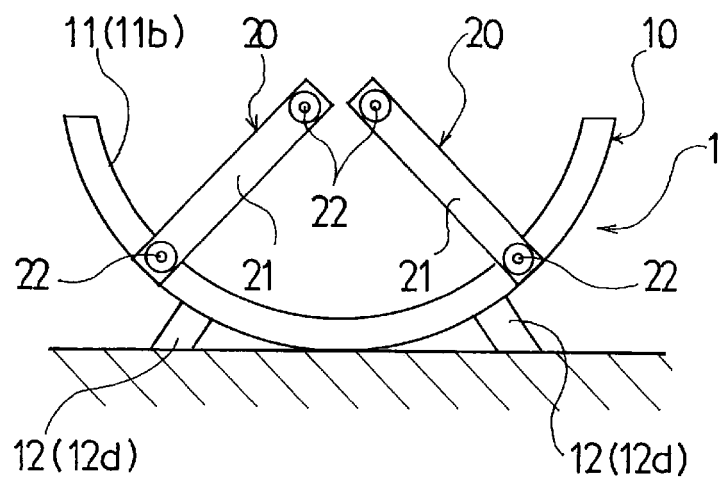
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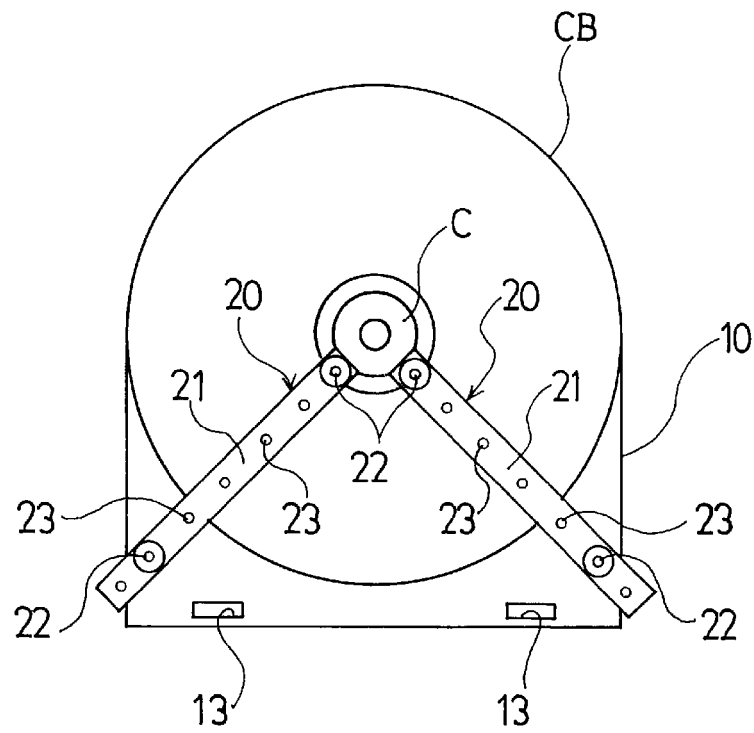
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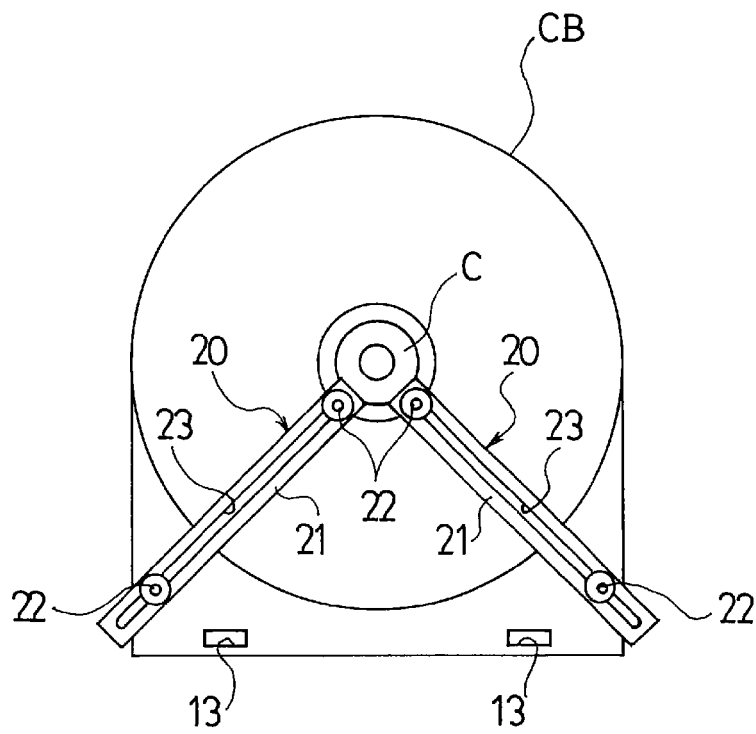
[図7]



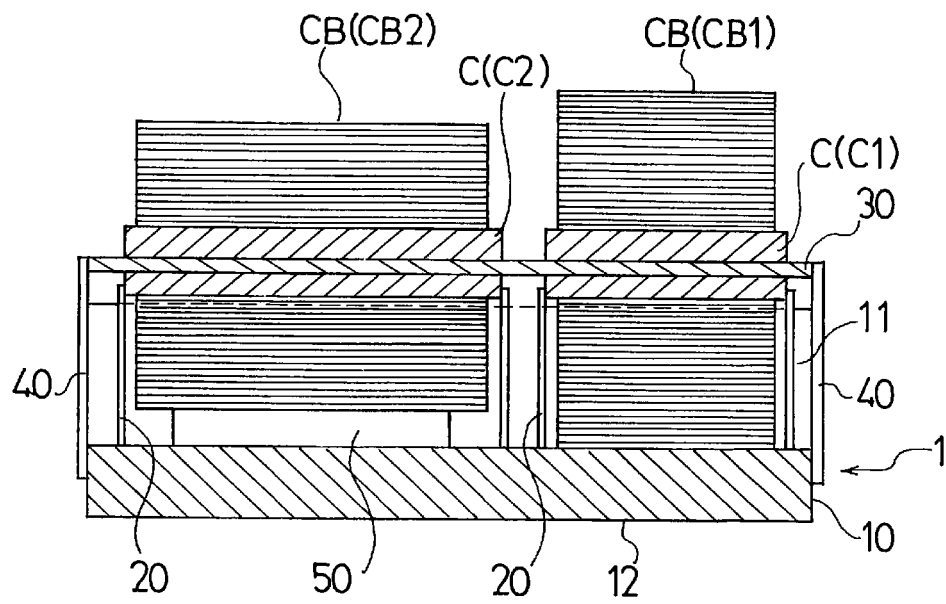
[図8]



[図9]



[図10]



[図11]

